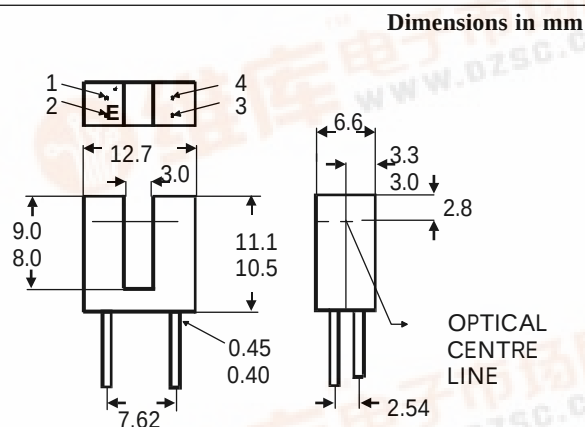
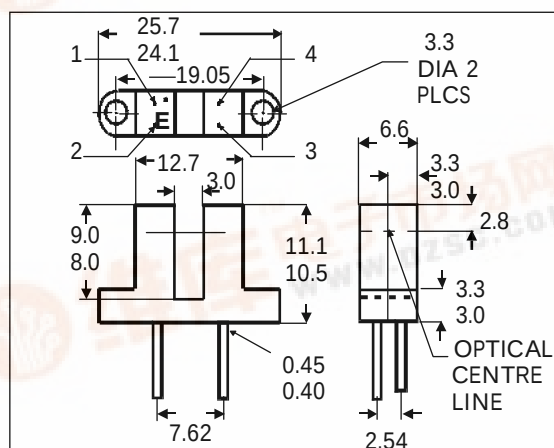


ISTS100
ISTS200



1mm APERTURE OPTO-ELECTRONIC SINGLE CHANNEL SLOTTED INTERRUPTER SWITCHES WITH TRANSISTOR SENSORS



ISTS200

ISTS100

DESCRIPTION

The ISTS100, ISTS200 opaque photointerrupters are single channel switches consisting of a Gallium Arsenide infrared emitting diode and a NPN silicon photo transistor mounted in a polycarbonate housing. The package is designed to optimise the mechanical resolution, coupling efficiency, ambient light rejection, cost and reliability. Operating on the principle that objects opaque to infrared will interrupt the transmission of light between an infrared emitting diode and a photo sensor switching the output from an "ON" state to an "OFF" state.

FEATURES

- High Gain
- 3mm Gap between LED and Detector
- Polycarbonate case protected against ambient light

APPLICATIONS

- Copiers, Printers, Facsimilies, Record Players, Cassette Decks, Optoelectronic Switches

ABSOLUTE MAXIMUM RATINGS (25°C unless otherwise specified)

Storage Temperature _____ -40°C to + 85°C
Operating Temperature _____ -25°C to + 85°C
Lead Soldering Temperature
(1/16 inch (1.6mm) from case for 10 secs) 260°C

INPUT DIODE

Forward Current _____ 50mA
Reverse Voltage _____ 5V
Power Dissipation _____ 75mW

OUTPUT TRANSISTOR

Collector-emitter Voltage BV_{CEO} _____ 30V
Emitter-collector Voltage BV_{ECO} _____ 5V
Collector Current I_C _____ 20mA
Power Dissipation _____ 75mW

ISOCOM COMPONENTS LTD

Unit 25B, Park View Road West,
Park View Industrial Estate, Brenda Road
Hartlepool, Cleveland, TS25 1YD
Tel: (01429) 863609 Fax : (01429) 863581

ISOCOM INC

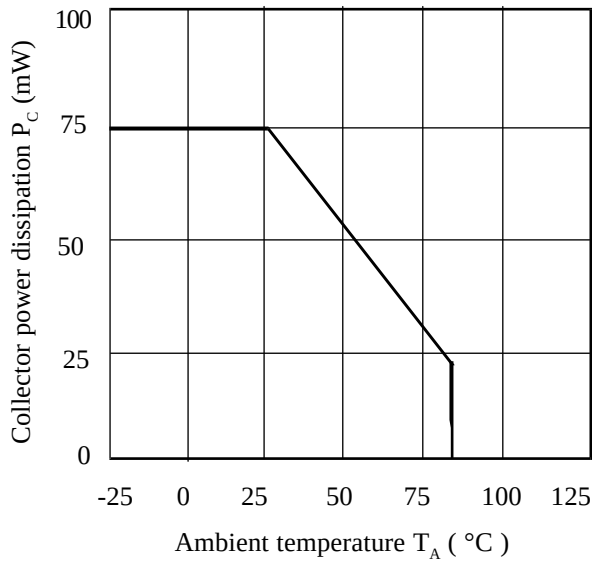
720 E., Park Boulevard, Suite 104,
Plano, TX 75074 USA
Tel: (972) 423-5521
Fax: (972) 422-4549

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ Unless otherwise noted)

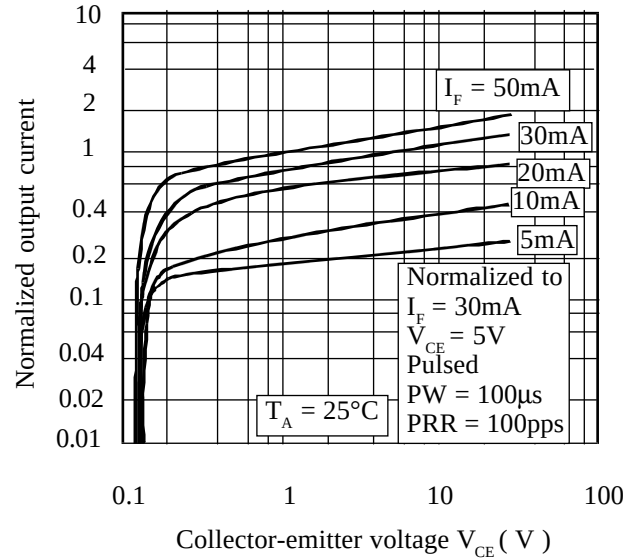
PARAMETER		MIN	TYP	MAX	UNITS	TEST CONDITION
Input	Forward Voltage (V_F)	5	1.2	1.7	V	$I_F = 50\text{mA}$ $I_R = 100\mu\text{A}$ $V_R = 5\text{V}$
	Reverse Voltage (V_R)				V	
	Reverse Current (I_R)			100	μA	
Output	Collector-emitter Breakdown (BV_{CEO}) (Note 1)	30			V	$I_C = 1\text{mA}$
	Emitter-collector Breakdown (BV_{ECO})	5			V	$I_E = 100\mu\text{A}$
	Collector-emitter Dark Current (I_{CEO})			100	nA	$V_{CE} = 10\text{V}$
Coupled	On-State Collector Current $I_C (_{ON})$ (Note 1)	1.9			mA	$30\text{mA } I_F, 5\text{V } V_{CE}$
	Collector-emitter Saturation Voltage $V_{CE(SAT)}$				0.4	V $30\text{mA } I_F, 1.8\text{mA } I_C$
	Turn-on Time t_{on} Turn-off Time t_{off}				8 50 μs μs	$V_{CC} = 5\text{V},$ $I_F = 30\text{mA}, R_L = 2.5\text{k}\Omega$

Note 1 Special Selections are available on request. Please consult the factory.

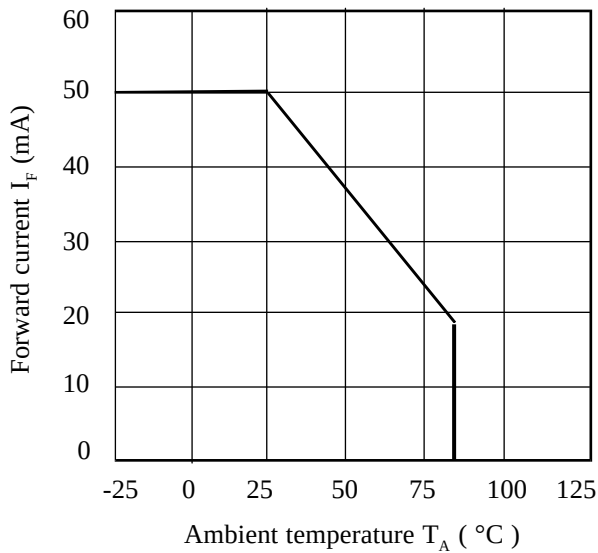
Collector Power Dissipation vs. Ambient Temperature



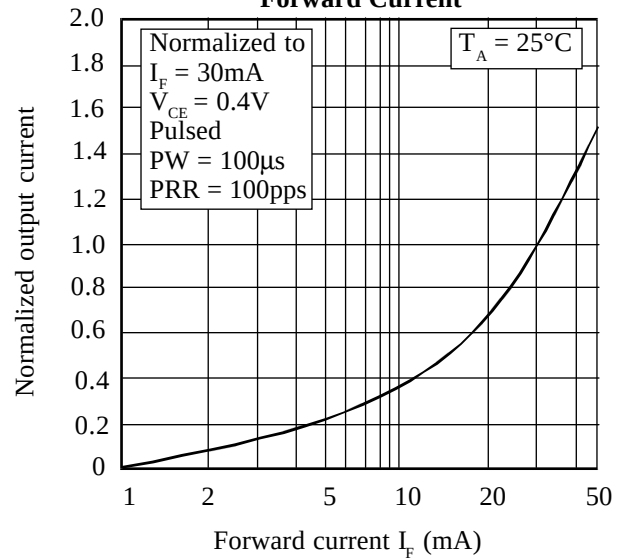
Normalized Output Current vs. Collector-emitter Voltage



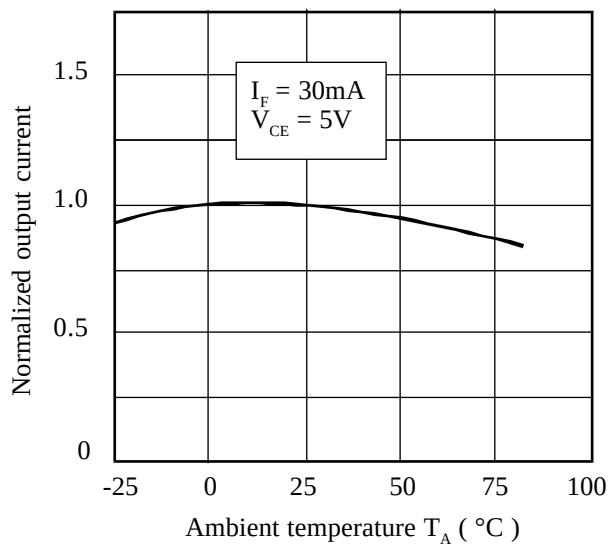
Forward Current vs. Ambient Temperature



Normalized Output Current vs. Forward Current



Normalized Output Current vs. Ambient Temperature



Collector-emitter Saturation Voltage vs. Ambient Temperature

